

REMARKS

The claims, as amended, call for the formation of the implanted species in the barrier layer and the dielectric, but not in the substrate to any substantial extent. Thus, the implanted species may be effective to alter, for example, etch rates of the barrier layer and the dielectric without adversely affecting the semiconductor substrate.

Note that the cited patent application to Hong is explicit that the implanted nitrogen species be implanted through the layers 202, 201, and down well into the substrate 200 to form the layer 200a, shown in Figure 2E. This is, apparently, to avoid interfering with the region that would become the source and drain, indicated at 110, in Figure 1E.

Thus, the cited patent application is clearly distinguishable. Similarly, the previously cited reference to Kamath also teaches the implant going into the substrate 100 as indicated at 120. See Kamath at column 6, lines 22-29.

Therefore, in view of these remarks, the application should now be in condition for allowance.

Respectfully submitted,

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